



R-C Thermal Model Parameters

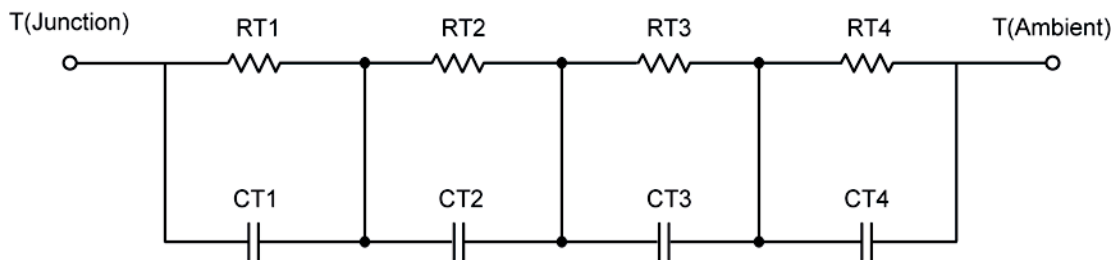
DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	41.4159	N/A	16.5114
RT2	43.1519	N/A	33.8852
RT3	14.6377	N/A	28.7965
RT4	55.7945	N/A	5.8069
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	8.9899 m	N/A	4.8332 m
CT2	30.3105 m	N/A	40.5991 m
CT3	759.4132 u	N/A	10.4477 m
CT4	1.5243	N/A	200.0630 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	18.4474	N/A	5.7732
RF2	34.1580	N/A	4.8167
RF3	47.4727	N/A	36.8986
RF4	54.9219	N/A	37.5115
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	707.2711 u	N/A	170.0542 u
CF2	5.7896 m	N/A	1.4686 m
CF3	8.9087 m	N/A	1.7632 m
CF4	1.5521	N/A	24.0455 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

